

said polishing surface having a second region [integral with said polishing surface, said second region adapted to frictionally contact said wafer];

a first underlying layer disposed beneath said first region, said first underlying layer adapted to achieve a first polishing effect in said first region; and

B1 a second underlying layer disposed beneath said second region, said second underlying layer adapted to achieve a second polishing effect in said second region such that said wafer polishing machine achieves a customized process effect by selectively moving said wafer frictionally against said first region and said second region.

Please cancel Claim 6 without prejudice.

10. (Amended) A multi-region polishing pad adapted for use in a wafer polishing machine, said multi-region polishing pad comprising:

a polishing pad adapted for use in a wafer polishing machine;

B2 a polishing surface of an overlying layer included in said polishing pad, said overlying layer being a uniform homogenous layer across the area of said polishing surface, said polishing surface adapted to frictionally contact a wafer in said wafer polishing machine;

said polishing surface having a plurality of regions [integral with said polishing surface, said plurality of regions each adapted to frictionally contact said wafer], each of said plurality of regions adapted to achieve a specific process effect such that said wafer polishing machine achieves a multi-region process effect by selectively moving said wafer frictionally against said plurality of regions; and

B2
a plurality of underlying layers included in said polishing pad, said plurality of underlying layers corresponding to said plurality of regions, each of said plurality of underlying layers adapted to achieve said specific process effect in said plurality of regions.

Please cancel Claim 14 without prejudice.